

BCW33LT1G, SBCW33LT1G

General Purpose Transistor

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	32	Vdc
Collector – Base Voltage	V_{CBO}	32	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

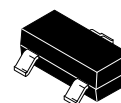
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

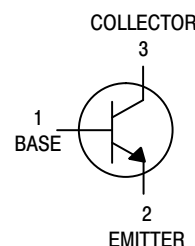


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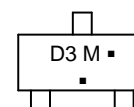
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SOT-23
(TO-236)
CASE 318-08
STYLE 6



MARKING DIAGRAM



D3 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW33LT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SBCW33LT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
BCW33LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I _C = 2.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	32	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 10 μA _{dc} , I _B = 0)	V _{(BR)CBO}	32	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	5.0	–	V _{dc}
Collector Cutoff Current (V _{CB} = 32 V _{dc} , I _E = 0) (V _{CB} = 32 V _{dc} , I _E = 0, T _A = 100°C)	I _{CBO}	– –	100 10	nA _{dc} μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = 2.0 mA _{dc} , V _{CE} = 5.0 V _{dc})	hFE	420	800	–
Collector–Emitter Saturation Voltage (I _C = 10 mA _{dc} , I _B = 0.5 mA _{dc})	V _{CE(sat)}	–	0.25	V _{dc}
Base–Emitter On Voltage (I _C = 2.0 mA _{dc} , V _{CE} = 5.0 V _{dc})	V _{BE(on)}	0.55	0.70	V _{dc}

SMALL–SIGNAL CHARACTERISTICS

Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	4.0	pF
Noise Figure (V _{CE} = 5.0 V _{dc} , I _C = 0.2 mA _{dc} , R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

EQUIVALENT SWITCHING TIME TEST CIRCUITS

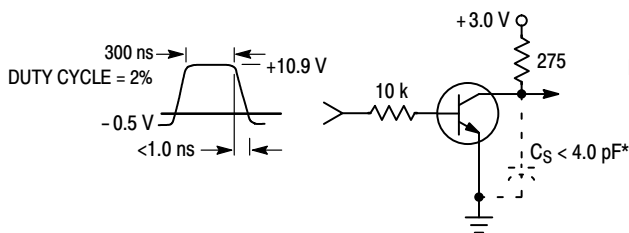


Figure 1. Turn–On Time

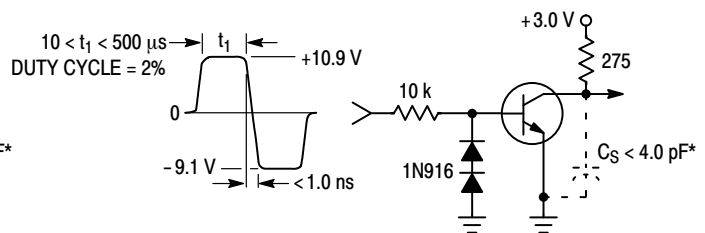


Figure 2. Turn–Off Time

*Total shunt capacitance of test jig and connectors

BCW33LT1G, SBCW33LT1G

TYPICAL NOISE CHARACTERISTICS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$)

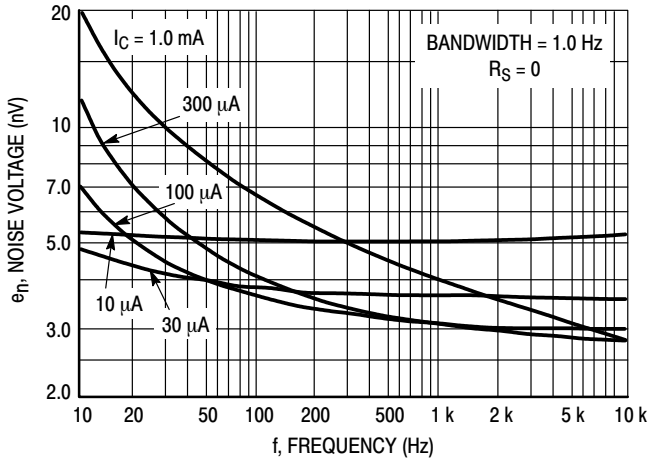


Figure 3. Noise Voltage

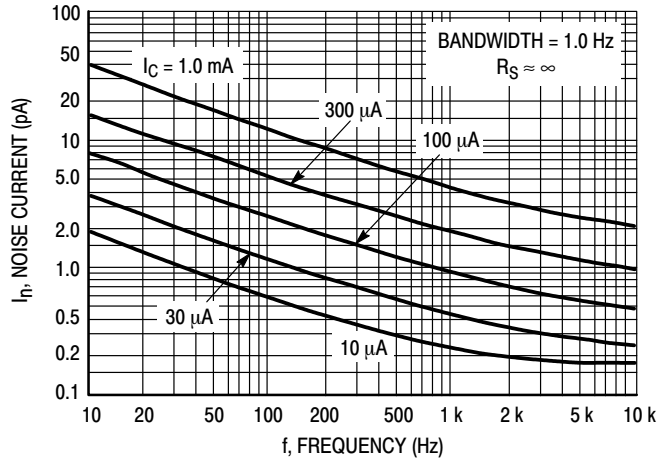


Figure 4. Noise Current

NOISE FIGURE CONTOURS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$)

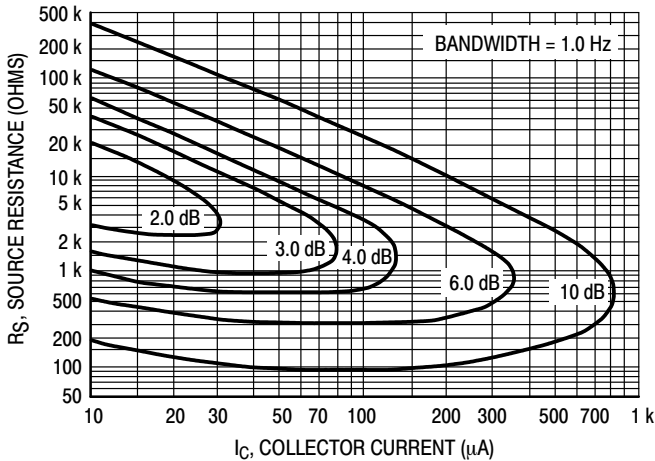


Figure 5. Narrow Band, 100 Hz

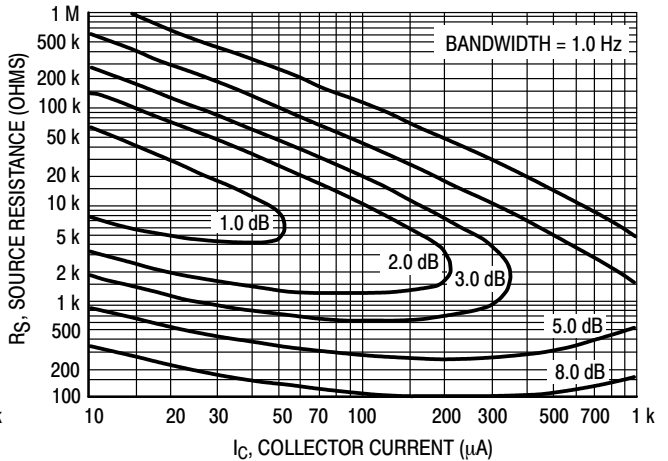


Figure 6. Narrow Band, 1.0 kHz

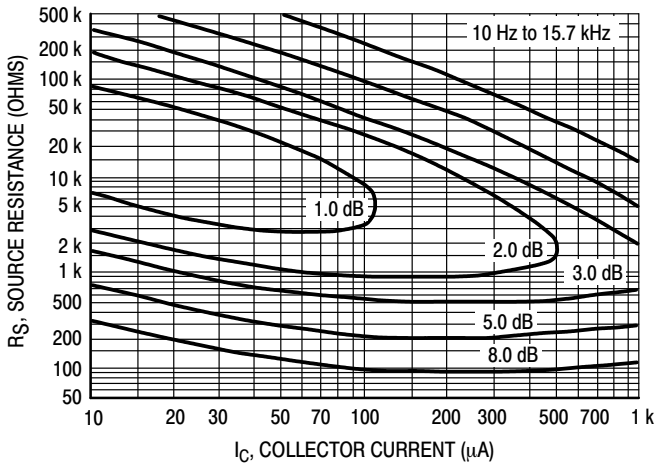


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left(\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

I_n = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant (1.38×10^{-23} j/°K)

T = Temperature of the Source Resistance (°K)

R_S = Source Resistance (Ohms)

BCW33LT1G, SBCW33LT1G

TYPICAL STATIC CHARACTERISTICS

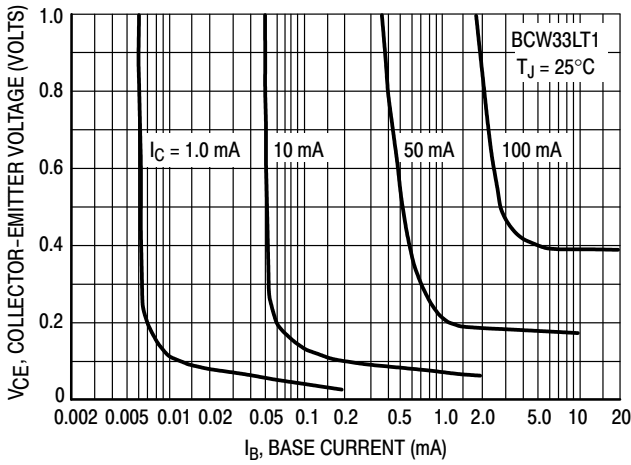


Figure 8. Collector Saturation Region

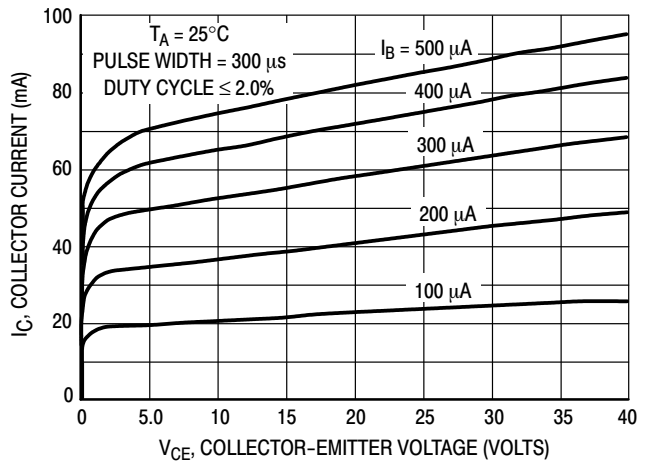


Figure 9. Collector Characteristics

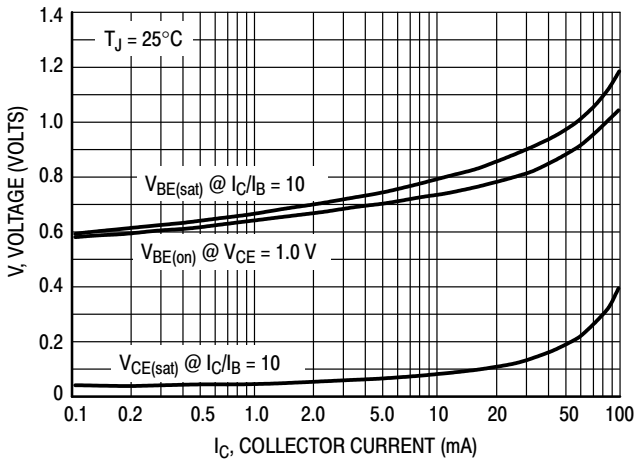


Figure 10. "On" Voltages

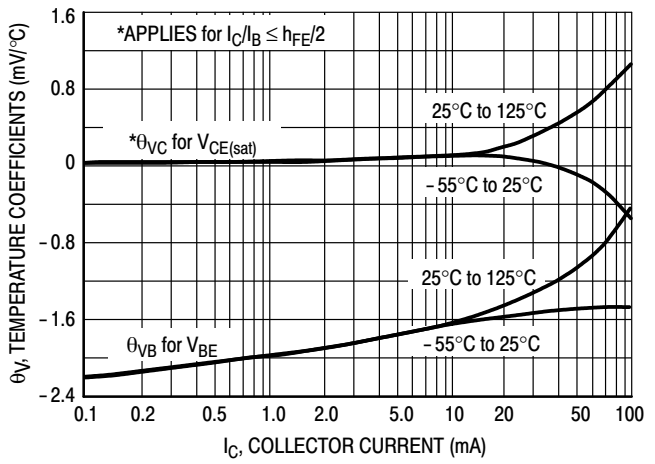


Figure 11. Temperature Coefficients

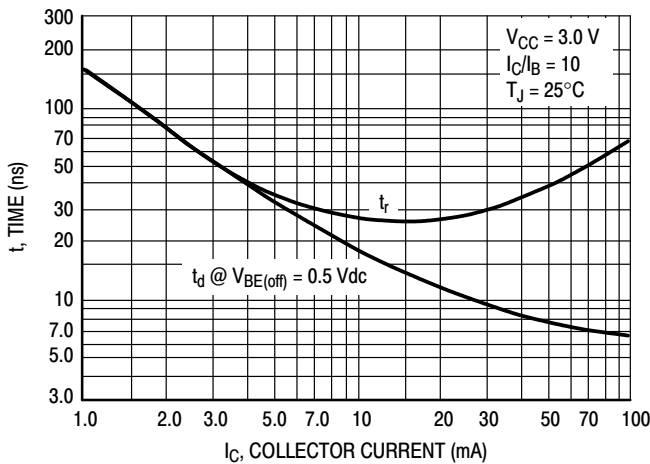


Figure 12. Turn-On Time

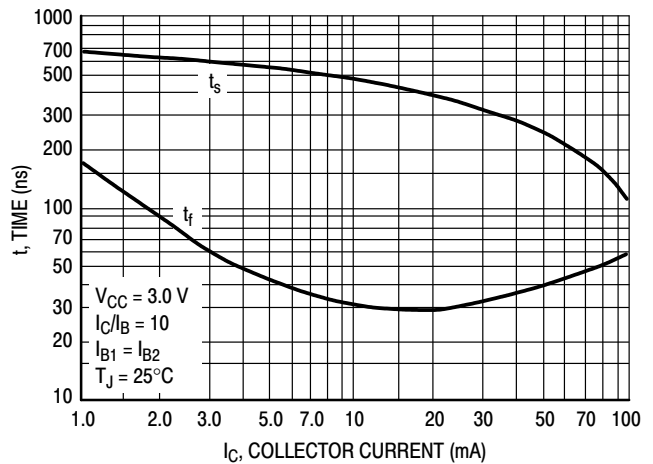


Figure 13. Turn-Off Time

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TYPICAL DYNAMIC CHARACTERISTICS

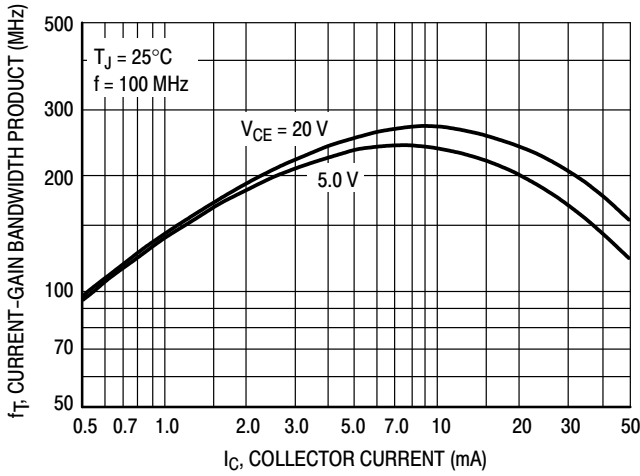


Figure 14. Current-Gain — Bandwidth Product

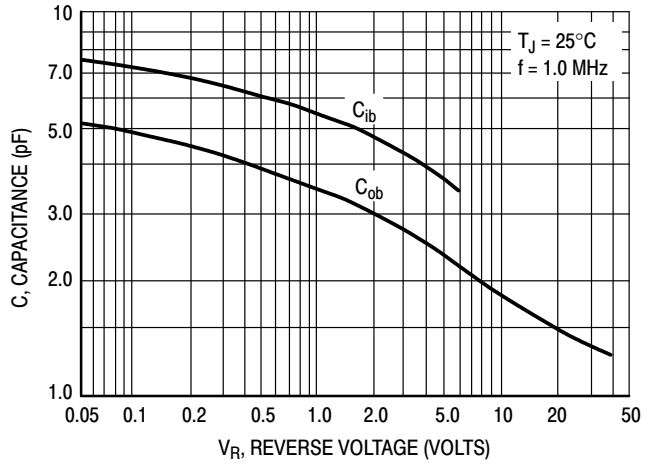


Figure 15. Capacitance

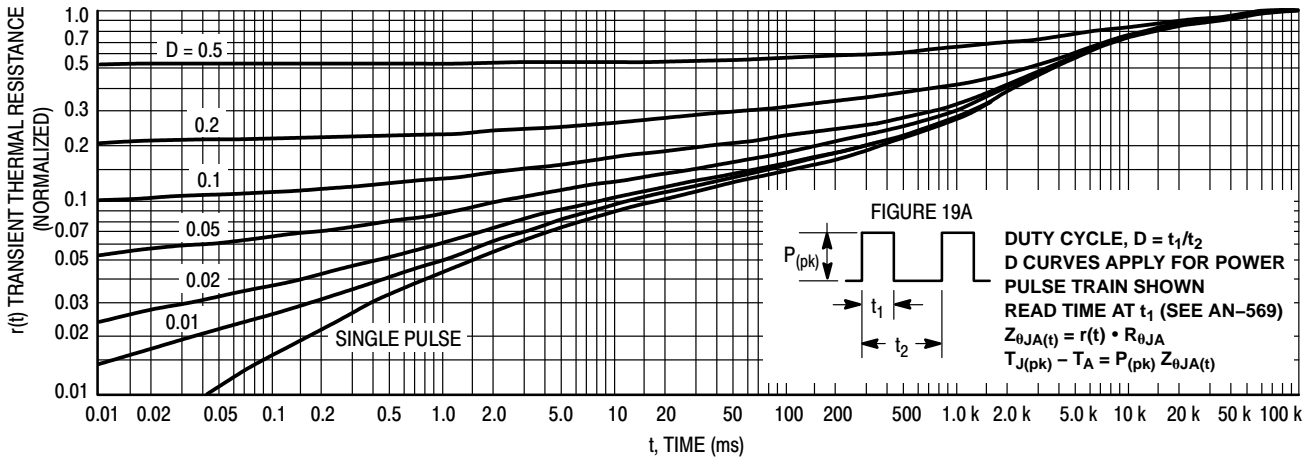


Figure 16. Thermal Response

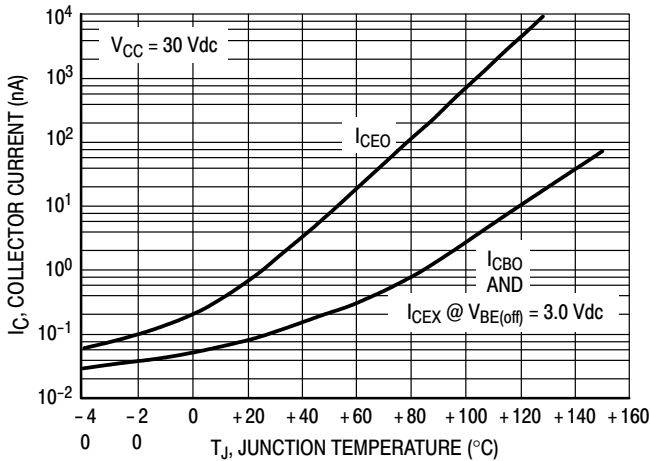


Figure 16A.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 16A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 16 was calculated for various duty cycles.

To find $Z_{\theta JA}(t)$, multiply the value obtained from Figure 16 by the steady state value $R_{\theta JA}$.

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$ ms, $t_2 = 5.0$ ms. ($D = 0.2$)

Using Figure 16 at a pulse width of 1.0 ms and $D = 0.2$, the reading of $r(t)$ is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see AN-569.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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